Corial D250L Recipes

Deposition Recipes

Recipe	Film	Dep. Temp [°C]	Dep. Rate [nm/min]	Refr. Index @ 677 nm	WER BHF 7:1, 21°C [nm/min]	WER KOH 40%, 60°C [nm/hr]	Unif. [%]	Stress [MPa]	Cleaning after
A_SiO2_Fast	SiO_x	320	405	1.47	219	-	0.5	-190	5 µm
A_SiO2-Fast_LF-150W	SiO_x	320	347.6	1.47	169	-	0.9	-346	5 µm
A_SiO2-Fast_LF-100W High_Stress	SiO_x	320	358.7	1.47	170.6	-	0.97	-338	5 µm
A_SiO2_High_Density	SiO_x	320	22.7	1.47	119	-	0.5	-318	5 µm
A_Si3N4_Fast	Si_xN_y	320	191.2	2	98	11.2	1.9	24	5 µm
A_Si3N4_High_Density	Si_xN_y	320	57.6	1.97	36.5	4	0.6	-100	5 µm
A_a-Si:H	a-Si:H	280	69	3.74	-	-	0.6	-280	500 nm / 1 wafer
A_SiC	SiC	300	30	2.68	-	-	1.36	-328	5 µm
A_aC	a-C	300	35.6	1.88	-	-	2.2	-242	500 nm
A_SiON_R2	SiO_xN_y	320	208.8	1.63	-	-	1	60.3	5 µm
A_SiON_R5	SiO_xN_y	320	175.5	1.69	-	-	0.9	31.6	5 µm
A_SiON_R7.25	SiO_xN_y	320	155.9	1.72	-	-	0.7	5.7	5 µm

Plasma Cleaning Recipes

Recipe	Film to be cleaned
B_Clean	SiO_x, Si_xN_y, a-Si:H, SiC, SiO_xN_y
B_Clean_aC	aC